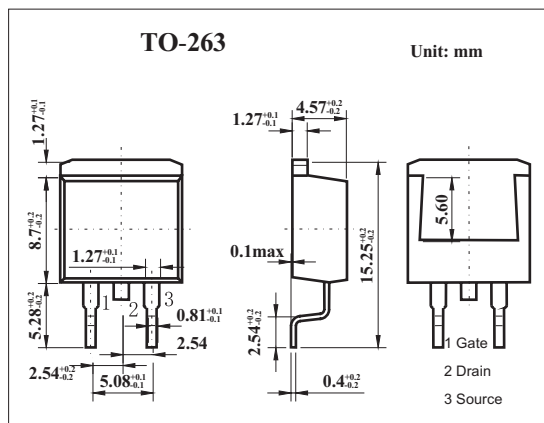
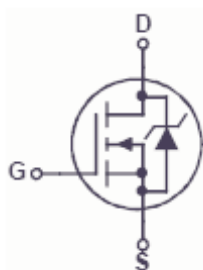


KDB2572(FDB2572)

■ Features

- $r_{DS(ON)} = 45m\Omega$ (Typ.), $V_{GS} = 10V$, $I_D = 9A$
- $Q_{g(tot)} = 26nC$ (Typ.), $V_{GS} = 10V$
- Low Miller Charge
- Low Q_{RR} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Drain to source voltage	V_{DS}	150	V	
Gate to source voltage	V_{GS}	± 20	V	
Drain current-Continuous	I_D	$T_c=25^\circ C$	29	A
		$T_A=25^\circ C$	4	A
Power dissipation	P_D	135	W	
		Derate above $25^\circ C$	0.9	W/ $^\circ C$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	43	$^\circ C/W$	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.11	$^\circ C/W$	
Channel temperature	T_{ch}	175	$^\circ C$	
Storage temperature	T_{stg}	-55 to +175	$^\circ C$	

KDB2572(FDB2572)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit	
Drain to source breakdown voltage	V _{DSS}	I _D =250μA, V _{GS} =0V	150			V	
Drain cut-off current	I _{DSS}	V _{DS} =120V, V _{GS} =0			1	μA	
		V _{DS} =120V, V _{GS} =0, T _C =150°C			250	μA	
Gate leakage current	I _{GSS}	V _{GS} =±20V			±100	nA	
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V	
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =10V, I _D =9A		0.045	0.054	Ω	
		V _{GS} =6V, I _D =4A		0.050	0.075		
		V _{GS} =10V, I _D =9A, T _C =175°C		0.126	0.146		
Input capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0, f=1MHZ		1770		pF	
Output capacitance	C _{oss}			183		pF	
Reverse transfer capacitance	C _{rss}			40		pF	
Total Gate Charge at 10V	Q _{g(TOT)}	V _{GS} = 0V to 10V		26	34	nC	
Threshold Gate Charge	Q _{g(TH)}	V _{GS} = 0V to 2V		3.3	4.3	nC	
Gate to Source Gate Charge	Q _{gs}	V _{DS} = 75 V, I _D = 9A, I _g =1.0mA		8		nC	
Gate Charge Threshold to Plateau	Q _{gs2}			5		nC	
Gate to Drain "Miller" Charge	Q _{gd}			6		nC	
Turn-On Time	t _{ON}					36	ns
Turn-On Delay Time	t _{d(ON)}	V _{DD} = 75 V, I _D = 9 A, V _{GS} = 10 V, R _{GEN} = 11 Ω		11		ns	
Rise Time	t _r			14		ns	
Turn-Off Delay Time	t _{d(OFF)}			31		ns	
Fall Time	t _f			14		ns	
Turn-Off Time	t _{OFF}					66	ns
Source to Drain Diode Voltage	V _{SD}		I _{SD} =9A			1.25	V
		I _{SD} =4A			1.0	V	
Reverse Recovery Time	t _{rr}	I _{SD} = 9A, di _{SD} /dt = 100A/μs			74	ns	
Reverse Recovered Charge	Q _{Rr}	I _{SD} = 9A, di _{SD} /dt = 100A/μs			169	nC	